

K Rim

List of Publications by Year in descending order

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| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | N-channel MOSFETs fabricated on He-implanted and annealed SiGe buffer layers. Solid-State Electronics, 2005, 49, 1669-1673. | 1.4 | 10 |
| 2 | The revolution in SiGe: impact on device electronics. Applied Surface Science, 2004, 224, 9-17. | 6.1 | 47 |
| 3 | Strained Si CMOS (SS CMOS) technology: opportunities and challenges. Solid-State Electronics, 2003, 47, 1133-1139. | 1.4 | 82 |
| 4 | Measurement of the effect of self-heating in strained-silicon MOSFETs. IEEE Electron Device Letters, 2002, 23, 360-362. | 3.9 | 135 |
| 5 | Effect of thermal processing on strain relaxation and interdiffusion in Si/SiGe heterostructures studied using Raman spectroscopy. Applied Physics Letters, 2001, 79, 2148-2150. | 3.3 | 57 |
| 6 | Fabrication and analysis of deep submicron strained-Si n-MOSFET's. IEEE Transactions on Electron Devices, 2000, 47, 1406-1415. | 3.0 | 328 |
| 7 | Admittance spectroscopy analysis of the conduction band offsets in Si/Si _{1-x} Ge _x and Si/Si _{1-y} Cy heterostructures. Journal of Applied Physics, 1999, 85, 985-993. | 2.5 | 23 |
| 8 | Measurement of the conduction band offsets in Si/Si _{1-x} Ge _x and Si/Si _{1-y} Cy heterostructures using metal-oxide-semiconductor capacitors. Journal of Applied Physics, 1999, 85, 978-984. | 2.5 | 27 |
| 9 | Evaluation of the valence band discontinuity of Si/Si _{1-x} Ge _x /Si heterostructures by application of admittance spectroscopy to MOS capacitors. IEEE Transactions on Electron Devices, 1998, 45, 494-501. | 3.0 | 26 |
| 10 | Comparison of Si/Si _{1-x} Ge _x and Si/Si _{1-y} Cy heterojunctions grown by rapid thermal chemical vapor deposition. Thin Solid Films, 1998, 321, 41-46. | 1.8 | 30 |
| 11 | Metal-oxide-semiconductor capacitance-voltage characteristics and band offsets for Si _{1-y} Cy/Si heterostructures. Applied Physics Letters, 1998, 72, 2286-2288. | 3.3 | 15 |
| 12 | Epitaxial Growth And Electronic Characterization Of Carboncontaining Silicon-Based Heterostructures. Materials Research Society Symposia Proceedings, 1998, 533, 263. | 0.1 | 6 |
| 13 | Characteristics of Surface-Channel Strained Si _{1-y} Cy-n-MOSFETS. Materials Research Society Symposia Proceedings, 1998, 533, 43. | 0.1 | 7 |
| 14 | Rapid Thermal Processing-Based Heteroepitaxy: Material and Device Challenges. Materials Research Society Symposia Proceedings, 1995, 387, 299. | 0.1 | 1 |
| 15 | Enhanced hole mobilities in surface-channel strained-Si p-MOSFETs. , 0, , . | | 60 |
| 16 | Strained Si NMOSFETs for high performance CMOS technology. , 0, , . | | 79 |